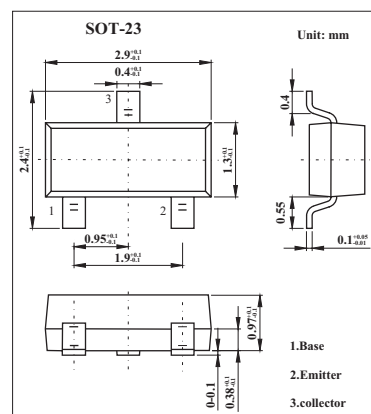


General Purpose Transistor

BCX71G

■ Features

- PNP Epitaxial Silicon Transistor



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-45	V
Collector-emitter voltage	V _{CEO}	-45	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-100	mA
Collector Power Dissipation	P _C	350	mW
Storage Temperature	T _{STG}	150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -2mA, I _B =0	-45			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -1μA, I _C =0	-5			V
Collector Cut-off Current	I _{CES}	V _{CE} = -32V, V _{BE} =0			-20	nA
DC Current Gain	h _{FE}	V _{CE} = -5V, I _C = -2mA	120		220	
		V _{CE} = -1V, I _C = -50μA	60			
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = -10mA, I _B = -0.25mA			-0.25	V
		I _C = -50mA, I _B = -1.25mA			-0.55	V
Base-Emitter Saturation Voltage	V _{BE (sat)}	I _C = -10mA, I _B = -0.25mA	-0.6		-0.85	V
		I _C = -50mA, I _B = -1.25mA	-0.68		-1.05	V
Base-Emitter On Voltage	V _{BE (on)}	V _{CE} = -5V, I _C = -2mA	-0.6		-0.75	V
Output Capacitance	C _{ob}	V _{CB} = -10V, I _E =0, f=1MHz				pF
Noise Figure	N _F	I _C =0.2mA, V _{CE} =5V, f=1KHz, R _S =2KΩ			6	dB
Turn On Time	t _{ON}	I _C = -10mA, I _{B1} = -1mA			150	ns
Turn Off Time	t _{OFF}	I _{B2} = -1mA, V _{BB} =3.6V, R _L =990Ω			800	ns

■ Marking

Marking	BG
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